# VS-30CTH02HN3

**Vishay Semiconductors** 



Hyperfast Rectifier, 2 x 15 FRED Pt®





#### VS-30CTH02HN3

PRODUCT SUMMARY								
Package	TO-220AB							
I <sub>F(AV)</sub>	2 x 15 A							
V <sub>R</sub>	200 V							
V <sub>F</sub> at I <sub>F</sub>	0.78 V							
t <sub>rr</sub> typ.	See Recovery table							
T <sub>J</sub> max.	175 °C							
Diode variation	Common cathode							

### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V					
Average rectified forward current	per diode		T <sub>C</sub> = 159 °C	15	^					
Average rectilied forward current	per device	IF(AV)		30	A					
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	200						
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C					

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-					
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	0.92	1.05	V				
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.78	0.85					
		V <sub>R</sub> = V <sub>R</sub> rated	-	-	10					
Reverse leakage current I <sub>R</sub>		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	5	300	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	57	-	pF				
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH				

Pb-free RoHS

COMPLIANT HALOGEN FREE Available

Revision: 03-Jul-17

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, \ dI_F/dt = 50$	A/μs, V <sub>R</sub> = 30 V	-	-	35				
	+	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100$	-	-	30	20				
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	26	-	ns			
		T <sub>J</sub> = 125 °C	l <sub>F</sub> = 15 A dl⊧/dt = 200 A/µs	-	40	-				
Peak recovery current	1	T <sub>J</sub> = 25 °C	$V_{\rm B} = 160 \text{ V}$	-	2.8	-	А			
Feak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	6.0	-	~			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	37	-	nC			
		T <sub>J</sub> = 125 °C		-	120	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Thermal resistance, per diode	e R <sub>thJC</sub>	Mounting surface, flat, smooth, and greased	-	-	1.1	°C/W				
Approximate weight			-	2	-	g				
Approximate weight			-	0.07	-	oz.				
Mounting torgue			6	-	12	kgf∙cm				
			5	-	10	(lbf · cm)				
Marking device		Case style TO-220AB		30CTH02H						

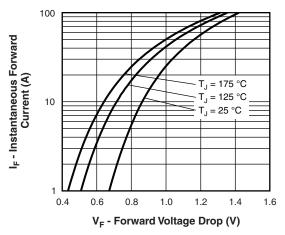


Fig. 1 - Typical Forward Voltage Drop Characteristics

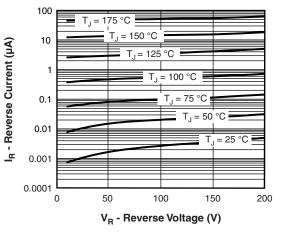


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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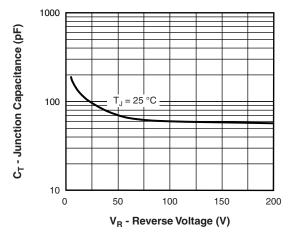


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

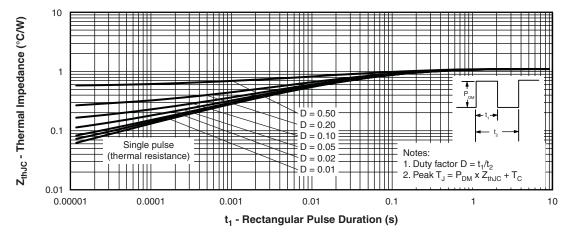
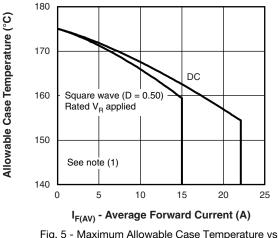
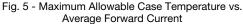
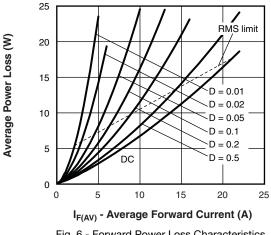


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



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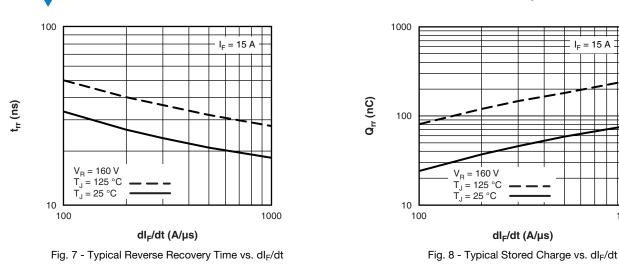
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# **VS-30CTH02HN3**

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#### Note

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<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

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 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{8}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

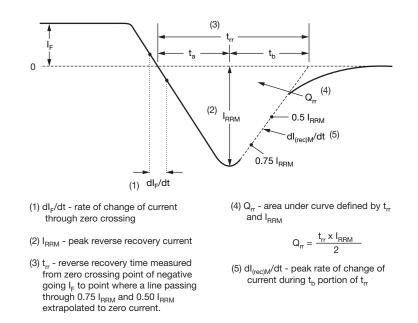


Fig. 9 - Reverse Recovery Waveform and Definitions





## **ORDERING INFORMATION TABLE**

Device code	VS-	30	С	т	н	02	н	N3
		2	3	4	5	6	7	8
	1 - 2 - 3 - 4 - 5 -	Curr C = T = H =	rent ratii commo TO-220 hyperfa	st recov	30 A) de ery			
	6 - 7 - 8 -	H = Envi	AEC-Q	ng (02 = 101 qua tal digit: en-free,	lified		nt, and	totally

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-30CTH02HN3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions	TO-220AB	www.vishay.com/doc?95222						
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028						

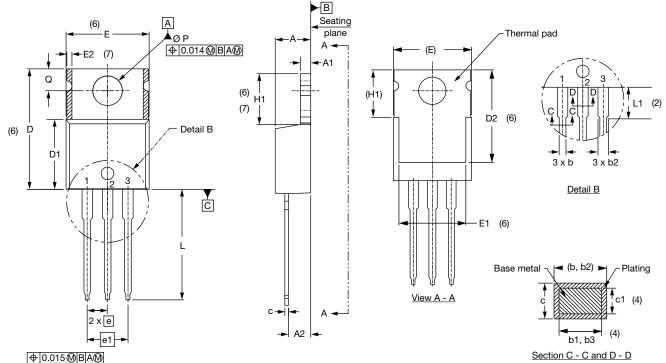
## **Outline Dimensions**



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**TO-220AB** 

## **DIMENSIONS** in millimeters and inches



Lead tip

Conforms to JEDEC<sup>®</sup> outline TO-220AB

SYMBOL	MILLIMETERS		INCHES			SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
STIVIDUL	MIN.	MAX.	MIN.	. MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
с	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimensions: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

<sup>(7)</sup> Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

(8) Outline conforms to JEDEC<sup>®</sup> TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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